Synchronous Buck DC/DC Converter

Features

- ➢ Up to 95% Efficiency
- Current Mode Operation for Excellent Line and Load Transient Response
- > 700mA Output Current
- Low Quiescent Current: 200µA
- \succ Output Voltage: 0.6V \sim 5.5V
- > Automatic PWM/PFM Mode Switching
- > No Schottky Diode Required
- Frequency Operation: 1.0MHz for Fixed
 Output Voltage and 1.4MHz for Adjustable
 Output Voltage
- Short-Circuit Protection
- Shutdown Quiescent Current: <1µA</p>
- Low Profile TSOT/ SOT-23-5L Package (lead-free packaging is now available)

Applications

- Digital cameras and MP3
- Palmtop computers / PDAs
- Cellular phones
- > Wireless handsets and DSL modems
- Portable media players
- PC cards

Description

The JTMH1001 is high efficiency synchronous, PWM step-down DC/DC converters working under an input voltage range from 2.2V to 5.5V. This feature makes the JTMH1001 suitable for single Li-Lon battery-powered applications. 100% duty cycle capability extends battery life in portable devices, while the quiescent current is 200µA with no load, and drops to <1µA in shutdown.

The internal synchronous switch is desired to increase efficiency without an external Schottky diode. The 1.0MHz/1.4MHz switching frequency allows the using of tiny, low profile inductors and ceramic capacitors, which minimized overall solution footprint.

The JTMH1001 converters are available in the industry standard TSOT/SOT-23-5L power packages (or upon request).

Order Information

JTMH1001 – 1) 2 3:

SYMBOL	DESCRIPTION			
	Denotes Output Voltage:			
	A: Adj			
1	K: 1.2V			
	B: 1.5 V			
	C: 1.8V			
	G: 3.3V			
2	Denotes Package Type:			
	E: SOT-23-5L			
3	Internal Definition			

Note: Only suitable for three-suffix letter products. Except JTMH1001-AETC, the "ET" means TSOT-23-5L Packages and the "C" is defined by internal.

Typical Application Circuit

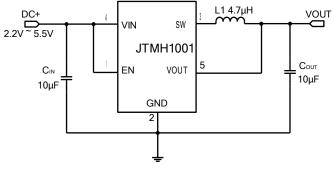
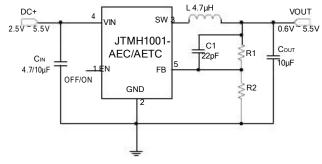


Figure 1: Fixed Voltage Converter

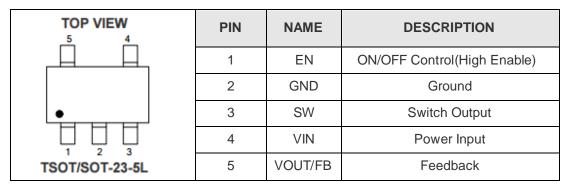


 $VOUT = 0.6V \cdot [1 + (R1/R2)].$

Figure 2: Adjustable Voltage Converter

Model	VOUT (V)	VIN (V)
JTMH1001-AEC	0.6 \sim 5.5	2.5 \sim 5.5
JTMH1001-AETC	0.6 \sim 5.5	2.5 \sim 5.5
JTMH1001-KEC	1.2	2.2 \sim 5.5
JTMH1001-BEC	1.5	2.5 \sim 5.5
JTMH1001-CEC	1.8	$2.5\sim5.5$
JTMH1001-GEC	3.3	$3.4~\sim~5.5$

Pin Assignment and Description



Absolute Maximum Ratings (Note 1)

Power Dissipation	Internally limited
Input Voltage	0.3V \sim +6V
Output Voltage	0.3V \sim +6V
EN,SW Pin Voltage	0.3V \sim (VIN+0.3)V
SW Pin Current	1.3A
Operating Temperature Range(Note 2)	40°C \sim +85°C
Junction Temperature	40°C \sim +125°C
Storage Temperature Range	65℃ ~ +150℃
Lead Temperature (Soldering,10 sec.)	+ 265 ℃
	Input Voltage Output Voltage EN,SW Pin Voltage SW Pin Current Operating Temperature Range(Note 2) Junction Temperature Storage Temperature Range

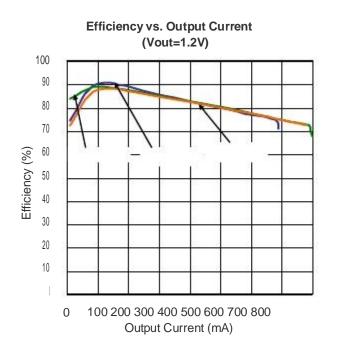
Note 1: Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.

Note 2: The JTMH1001 is guaranteed to meet performance specifications from 0°C to 85°C. Specifications over the -40°C to 85°C operating temperature range are assured by design, characterization and correlation with statistical process controls.

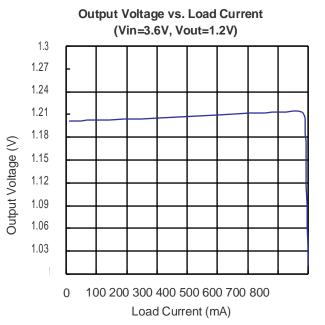
Electrical Characteristics

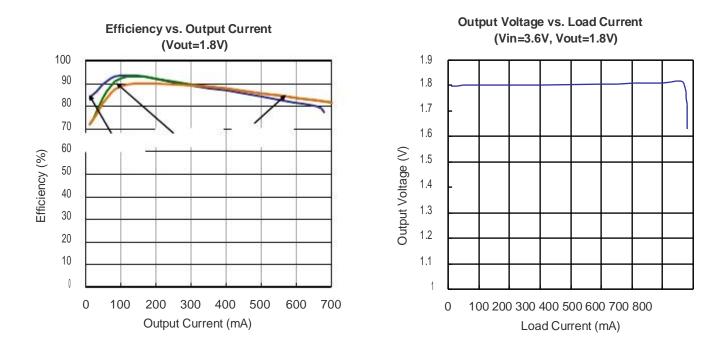
SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNITS
Vin	Input Voltage		2.2		5.5	V
ΔVουτ	Output Voltage Accuracy (For Fixed Output Voltage)	lout=100mA	-2		+2	%
Vout	Adjustable Output Range		0.6		5.5	V
Vfb	Regulated Voltage	TA = 25℃	0.588	0.6	0.612	V
ΔVfb	Vref	Vin=2.5V \sim 5.5V		0.03	0.4	%/V
lгв	Feedback Current				±30	nA
lq	Quiescent Current	Vfb = 0.5V or Vout = 90%, Iload = 0A		200		μA
Іѕнтр	Shutdown Current	VEN=0V, VIN=4.2V, For Fixed Output Voltage		0.1	1	μA
ISHID S	Shutdown Current	VEN=0V, VIN=5V, For Adjustable Output Voltage		0.5	1	μA
fosc	Oscillator Frequency	Vout=100%, For Fixed Output Voltage		1.0		MHz
1000		V _{FB} =0.6V, For Adjustable Output Voltage		1.4		MHz
Ірк	Peak Inductor Current	VFB=0.5V or Vout= 90%	0.75	0.9	1.1	А
Rpfet	RDS(ON) of P-Channel FET	Isw=100mA		0.3		Ω
RNFET	RDS(ON) of N-Channel FET	Isw=-100mA		0.39		Ω
ΔV LINE	Vout Line Regulation	VIN=(VOUT+0.5) to 5.5V		0.03	0.3	%/V
ΔV load	Vout Load Regulation	0mA ≤ louτ ≤ 100mA		0.33		%
EFFI	Efficiency	When connected to extra components , VIN =VEN=2.7V, VOUT=2.5V, IOUT =100mA		90	95	%

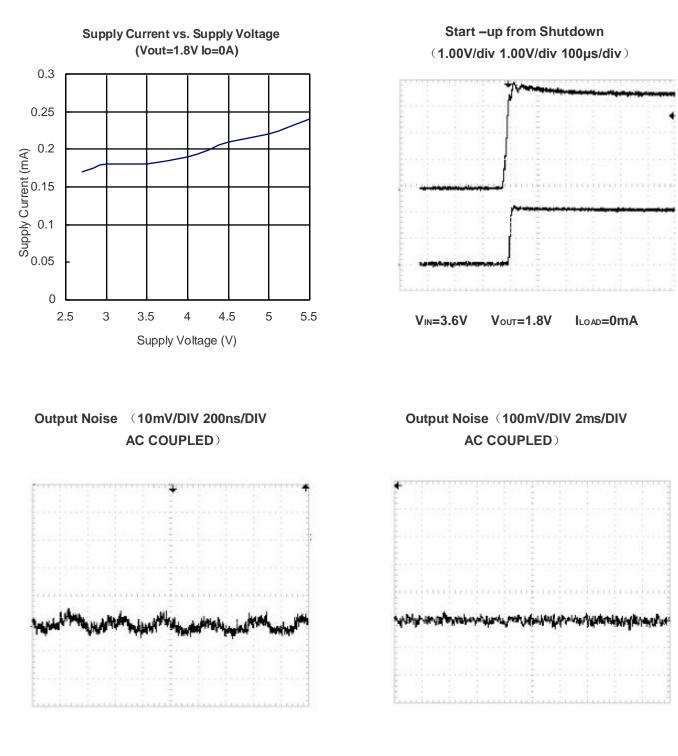
Operating Conditions: TA=25 $^\circ\!\mathrm{C}$, VIN = Vout + 1V, unless otherwise specified.



Typical Performance Characteristics







VIN=3.6V Vo

Vout=1.8V ILOAD=200mA

VIN=3.6V VOUT=1.8V ILOAD=0mA

Pin Functions

EN (Pin 1): En Control Input. Forcing this pin above 1.5V enables the part. Forcing this pin below 0.6V can shuts down the device. In shutdown, all functions are disabled drawing <1µA supply current. Do not leave EN floating.

GND (Pin 2): Ground Pin.

SW (Pin 3): Switch Node Connection to Inductor. This pin connects to the drains of the internal main and synchronous power MOSFET switches.

VIN (Pin 4): Main Supply Pin. A 10µF ceramic VIN capacitor recommended must be closely decoupled to GND.

VOUT/FB (Pin 5): Feedback Pin. In the nonadjustable version, the output voltage is fixed. In the adjustable version, the FB pin receives the feedback voltage from an external resistive divider across the output. The output voltage is set by a resistive divider according to the following formula: $Vout = 0.6V \cdot [1 + (R1/R2)]$.

Application Information

The basic JTMH1001 application circuit is shown in Typical Application Circuit. External component selection is determined by the maximum load current and begins with the selection of the inductor value and operating frequency followed by CIN and COUT.

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1μ H to 4.7μ H. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher VIN or VOUT also increases the ripple current as shown in the equation. A reasonable starting point for setting ripple current is $I \perp = 280$ mA (40% of 700mA).

$$\Delta I_L = \frac{1}{(f)(L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right)$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 840mA rated inductor should be enough for most applications (700mA + 140mA). For better efficiency, choose a low DC-resistance inductor.

Different core materials and shapes will change the size/current and price/current relationship of an inductor. Toroid or shielded pot cores in ferrite or perm alloy materials are small and don't radiate much energy, but generally cost more than powdered iron core inductors with similar electrical characteristics. The choice of which style inductor to use often depends more on the price vs. size requirements and any radiated field/EMI requirements than on what the JTMH1001 requires to operate.

Output and Input Capacitor Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle Vout/VIN. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN} \text{ required } I_{RMS} \cong I_{OMAX} \frac{\left[V_{OUT} (V_{IN} - V_{DUT})\right]^{1/2}}{V_{IN}}$$

This formula has a maximum at $V_{IN} = 2V_{OUT}$, where $I_{RMS} = I_{OUT}/2$. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Always consult the manufacturer if there is any question.

The selection of Cout is driven by the required effective series resistance (ESR).

Typically, once the ESR requirement for Cout has been met, the RMS current rating generally far exceeds the IRIPPLE(P-P) requirement. The output ripple ΔV out is determined by:

$$\Delta V_{OUT} = \Delta I_{L} \left(\text{ESR} + \frac{1}{8\text{fC}_{OUT}} \right)$$

Where f = operating frequency, Cout = output capacitance and ΔI_L = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ΔI_L increases with input voltage.

Aluminum electrolytic and dry tantalum capacitors are both available in surface mount configurations. In the case of tantalum, it is critical that the capacitors are surge tested for use in switching power supplies. An excellent choice is the AVX TPS series of surface mount tantalum. These are specially constructed and tested for low ESR so they give the lowest ESR for a given volume. Other capacitor types include Sanyo POSCAP, Kemet T510 and T495 series, and Sprague 593D and 595D series. Consult the manufacturer for other specific recommendations.

Efficiency Considerations

The efficiency of a switching regulator is equal to the output power divided by the input power times 100%. It is often useful to analyze individual losses to determine what is limiting the efficiency and which change would produce the most improvement. Efficiency can be expressed as: Efficiency = 100% - (L1+ L2+ L3+ ...) where L1, L2, etc. are the individual losses as a percentage of input power. Although all dissipative elements in the circuit produce losses, two main sources usually account for most of the losses: VIN quiescent current and I₂R losses. The VIN quiescent current loss dominates the efficiency loss at very low load currents whereas the I₂R loss dominates the efficiency loss at medium to high load currents. In a typical efficiency plot, the efficiency curve at very low load currents can be misleading since the actual power lost is of no consequence.

1. The VIN quiescent current is due to two components: the DC bias current as given in the electrical characteristics and the internal main switch and synchronous switch gate charge currents. The gate charge current results from switching the gate capacitance of the internal power MOSFET switches. Each time the gate is switched from high to low to high again, a packet of charge ΔQ moves from VIN to ground. The resulting $\Delta Q/t$ is the current out of VIN that is typically larger than the DC bias current. In continuous mode, IGATECHG = f (QT+QB) where QT and QB are the gate charges of the internal top and bottom switches. Both the DC bias and gate charge losses are proportional to VIN and thus their effects will be more pronounced at higher supply voltages.

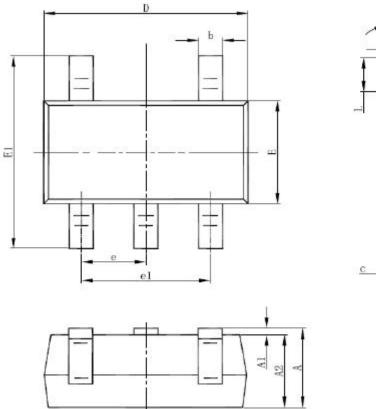
2. I₂R losses are calculated from the resistances of the internal switches, Rsw and external inductor RL. In continuous mode the average output current flowing through inductor L is "chopped" between the main switch and the synchronous switch. Thus, the series resistance looking into the SW pin is a function of both top and bottom MOSFET RDS(ON) and the duty cycle (DC) as follows: Rsw = RDS(ON)TOP x DC + RDS(ON)BOT x (1-DC) The RDS(ON) for both the top and bottom MOSFETs can be obtained from the Typical Performance Characteristics curves. Thus, to obtain I₂R losses, simply add Rsw to RL and multiply the result by the square of the average output current. Other losses including CIN and COUT ESR dissipative losses and inductor core losses generally account for less than 2% of the total loss.

PCB Layout Guidelines

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the JTMH1001. Check the following in your layout:

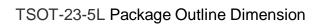
- 1. The power traces, consisting of the GND trace, the SW trace and the VIN trace should be kept short, direct and wide.
- 2. Put the input capacitor as close as possible to the device pins (VIN and GND).
- 3. SW node is with high frequency voltage swing and should be kept small area. Keep analog components away from SW node to prevent stray capacitive noise pick-up.
- 4. Connect all analog grounds to a command node and then connect the command node to the power ground behind the output capacitors.
- 5. Keep the (–) plates of CIN and COUT as close as possible.

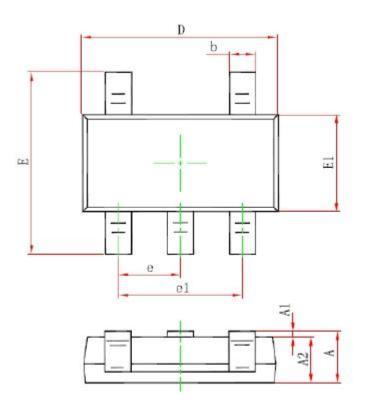
Packaging Information SOT-23-5L Package Outline Dimension

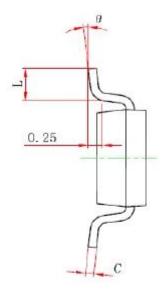


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C		

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
А	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950(BSC)		0.037(BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
А	0.0000	0.900		0.035
A1	0.020	0.090	0.001	0.004
A2	0.700	0.800	0.028	0.031
b	0.350	0.500	0.014	0.020
с	0.080	0.200	0.003	0.008
D	2.820	3.020	0.111	0.119
E1	1.600	1.700	0.063	0.067
E	2.650	2.950	0.104	0.116
e	0.95 (BSC)		0.037	(BSC)
e1	1.90 (BSC)		0.075	(BSC)
L	0.300	0.600	0.012	0.024
e	0 °	8°	0°	8°